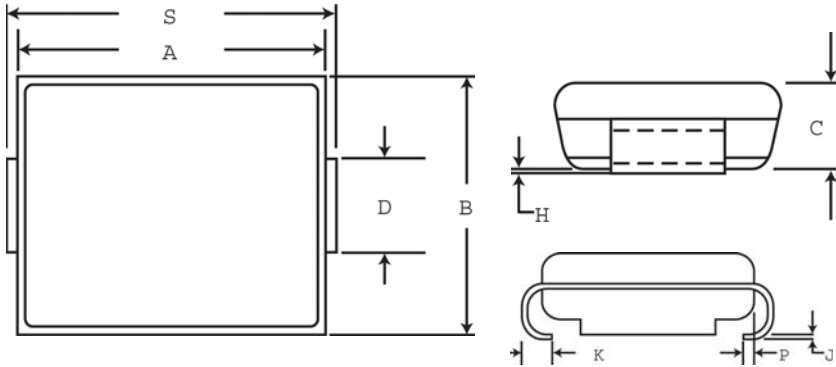
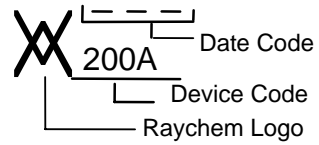


Specification Status: RELEASED

PHYSICAL DESCRIPTION



Marking:



A		B		C		D**		H		J		K	
MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
4.06	4.57	3.30	3.81	1.90	2.41	1.96	2.11	0.051	0.152	0.15	0.30	0.76	1.27
(0.160)	(0.180)	(0.130)	(0.150)	(0.075)	(0.095)	(0.077)	(0.083)	(0.002)	(0.006)	(0.006)	(0.012)	(0.030)	(0.050)

P	S	
REF	MIN	MAX
0.51	5.21	5.59
(0.020)	(0.205)	(0.220)

*Rounded off approximation

** D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

Other Physical Characteristics

- Form Factor: SMB (Surface Mount, JEDEC DO-214AA Package)
- Lead Material: Matte Tin Finish
- Encapsulation Material: Epoxy, meets UL94 V-0 requirements
- Solderability: per MIL-STD-750, Method 2026
- Solder Heat Withstand: per MIL-STD-750, Method 2031
- Solvent Resistance: per MIL-STD-750, Method 1022
- Mechanical Shock: per MIL-STD-750, Method 2016
- Vibration: per MIL-STD-750, Method 2056

Tape and Reel packaging per EIA 481-1

- Agency Recognition: UL
- Precedence: This specification takes precedence over documents referenced herein.
- CAUTION: Operation beyond the rated voltage or current may result in rupture, electrical arcing or flame.

Materials Information

- RoHS Compliant
- ELV Compliant

Directive 2002/95/EC
Compliant

Directive 2000/53/EC
Compliant

OBSOLETE
NOT the LATEST
REVISION

DEVICE RATINGS @ 25° C (Both Polarities)

Parameter	Symbol	Value	Units
Repetitive off-State Voltage, Maximum at $I_D = 5 \mu A$	VDM	200	V
Non-Repetitive Peak Impulse Current	TELCORDIA GR-1089 CORE 10x1000 μs	50	A
	TIA-968 lightning Type A Metallic 10/560 μs	70	A
Double exponential Waveform	TIA-968 lightning Type A Longit. 10/160 μs	100	A
	Telcordia GR-1089 Intrabuilding 2/10 μs	150	A
(Notes 1 and 2)	IEC61000-4-5 (Voc 1.2/50us) 8/20 μs	150	A
	ITU-T K.20/K.21 (Voc 10/700us) 5/310 μs	90	A
	TIA-968 lightning Type B (Voc 9/720us) 5/320 μs	90	A
Critical Rate of Rise of On-State Current Powered Pulse Amplifier, C=30 μF , V=600V Maximum 2x10 μs waveform, $V_{OC}=750V$, $I_{SC}=150A$ peak	di/dt	500	A/ μs
	di/dt	110	A/ μs

DEVICE THERMAL RATINGS

Storage Temperature Range	TSTG	-55 to 150	°C
Operating Temperature Range Blocking or conducting state	TA	-40 to 125	°C
Overload Junction Temperature Maximum; Conducting state only	TJ	+150	°C
Maximum Lead Temperature for Soldering Purpose; for 10 seconds	TL	+260	°C

ELECTRICAL CHARACTERISTICS Both polarities (T_J @ 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Units
Breakover Voltage (+25°C) ($dv/dt = 0.4kV/\mu sec$, $I_{SC}=900mA$, $V_{DC} = 500V$ (both polarities))	VBO	----	260	320	V
Breakover Voltage Temperature Coefficient	dVBO/dTJ	----	0.1	-----	%/°C
Off-State Current (VD1=50V)	ID1	----	-----	2.0	μA
(VD2=VDM)	ID2=IDM	----	-----	5.0	μA
On-State Voltage (IT=1A)	VT	----	-----	4.0	V
Breakover Current	IBO	----	-----	800	mA
Holding Current (Note 2)	IH	150	----	----	mA
Peak Onstage Surge Current (Measured @ 60Hz, 1 cycle, 600V)	ITSM	22	----	----	A
Critical Rate of Rise of Off-State Voltage (Linear waveform, $V_D = 0.8 X$ Rated V_{BO} , $T_J = +25^\circ C$)	dv/dt	2000	----	----	V/ μs
Capacitance (f=1.0 Mhz, 50V _{DC} bias, 1Vrms)	C1	----	18	----	pF
(f=1.0 Mhz, 2V _{DC} bias, 1Vrms)	C2	----	35	----	pF

Note 1. Allow cooling before test second polarity

Note 2. Measured under pulse conditions to reduce heating

VOLTAGE-CURRENT CHARACTERISTIC
